

Title (en)
FIELD-EFFECT TRANSISTOR AND METHOD FOR MANUFACTURING SAME

Title (de)
FELDEFFEKTTRANSISTOR UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)
TRANSISTOR À EFFET DE CHAMP, ET PROCÉDÉ DE FABRICATION ASSOCIÉ

Publication
EP 2660870 A4 20140305 (EN)

Application
EP 11853548 A 20111219

Priority

- JP 2010290516 A 20101227
- JP 2011079979 W 20111219

Abstract (en)
[origin: US2013032797A1] The present invention achieves a formation of a metal oxide film of a thin film transistor with a simplified process. The present invention is concerned with a method for manufacturing a field-effect transistor comprising a gate electrode, a source electrode, a drain electrode, a channel layer and a gate insulating layer wherein the channel layer is formed by using a metal salt-containing composition comprising a metal salt, a polyvalent carboxylic acid having a cis-form structure of —C(COOH)=C(COOH)— , an organic solvent and a water wherein a molar ratio of the polyvalent carboxylic acid to the metal salt is in the range of 0.5 to 4.0.

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Citation (search report)

- [XYI] US 2009127551 A1 20090521 - IMAI SHINJI [JP]
- [Y] JP 2003183009 A 20030703 - NICHIA KAGAKU KOGYO KK
- See references of WO 2012090891A1

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